

## ABSTRACT OF THE DISCLOSURE

A low reflective film is formed of, in sequence from a side in contact with a laser chip, a first dielectric film of a refractive index  $n_1$  and a thickness  $d_1$ , a second dielectric film of a refractive index  $n_2$  and a thickness  $d_2$ , a third dielectric film of a refractive index  $n_3$  and a thickness  $d_3$ , and a fourth dielectric film of a refractive index  $n_4$  and a thickness  $d_4$ , specifically, aluminum oxide  $Al_2O_3$  with a refractive index  $n_1 = 1.638$  is used for the first dielectric film, silicon oxide  $SiO_2$  with a refractive index  $n_2 = n_4 = 1.489$  for the second and fourth dielectric films, tantalum oxide  $Ta_2O_5$  with a refractive index  $n_3 = 2.063$  for the third dielectric film, respectively, resulting in a semiconductor laser device with a reflectance which is stably controllable.